

Guidelines for Abstract Preparation of EDISON 21 (Bold, 12 point, Times or Times New Roman)

A. Oiwa¹, N. Mori², and Y. Kamakura² (11 point, Times or Times New Roman)

¹*Institute of Scientific and Industrial Research, Osaka University, Osaka 567-0047, Japan*

²*Graduate School of Engineering, Osaka University*

Osaka 565-0871, Japan (11 point, Italic, Times or Times New Roman)

oiwa@sanken.osaka-u.ac.jp (11 point, Times or Times New Roman)

Camera-ready 1-page abstract should be prepared on an A4-size paper with 2 cm margins all around. The abstract must include the title of the paper, author(s), affiliation(s), address(es) and e-mail address. Use capital letters for the initial letter of each word except articles, prepositions and conjunctions. The main text should be typed with single-spaced and 11 point. List and numbers of all the references should be at the end of the abstract. When referring to them in the text, the reference number should be indicated by brackets, such as [1, 2]. The deadline of the submission is **March 15, 2019**.

The 21st International Conference on Electron Dynamics in Semiconductors, Optoelectronics and Nanostructures (EDISON) will be held in Nara, Japan, from July 14 (Sunday) through 19 (Friday), 2019. Since the first meeting was held in Modena, Italy, in 1973, this series of meetings have been organized regularly; Modena (1973), Denton (1977), Montpellier (1981), Innsbruck (1985), Boston (1987), Scottsdale (1989), Nara (1991), Oxford (1993), Chicago (1995), Berlin (1997), Kyoto (1999), Santa Fe (2001), Modena (2003), Chicago (2005), Tokyo (2007), Montpellier (2009), Santa Barbara (2011), Matsue (2013), Salamanca (2015), and Buffalo (2017). EDISON 21 will highlight the latest progress in the field of fundamental physics and applications of electron dynamics in semiconductors, optoelectronic devices, and nanostructures.



Fig. 1. EDISON 21 logo (10 point)

The scope of EDISON 21 covers nonequilibrium carrier dynamics in semiconductors, optoelectronics and nanostructure devices, with emphasis on the physics of transport and optical phenomena, including:

1. Nonequilibrium carrier transport in bulk and nanostructured materials
2. Nonequilibrium carrier transport in novel devices
3. Coherent/incoherent carrier dynamics and ultra-fast optical phenomena
4. Coherent carrier dynamics for quantum technologies
5. Terahertz phenomena in semiconductor materials and devices
6. Semiconductor-based spintronics
7. Mesoscopic phenomena in nanostructured materials and devices
8. Carrier dynamics in organic materials
9. Synthesis and electrical and optical properties of graphene and 2D van der Waals materials
10. Topological states of matter
11. Ultrafast carrier dynamics in energy-conversion processes
12. Energy harvesting from nanostructures
13. Nonequilibrium thermal transport in devices and nanostructures
14. Nonequilibrium carrier dynamics and fluctuations
15. Carrier dynamics in phononic and mechanical structures
16. Hot carrier effects in nanoplasmonic systems

References

- [1] T. Ando, A. B. Fowler, and F. Stern, *Rev. Mod. Phys.* **54**, 437 (1982).
- [2] C. Jacoboni and L. Reggiani, *Rev. Mod. Phys.* **55**, 645 (1983).